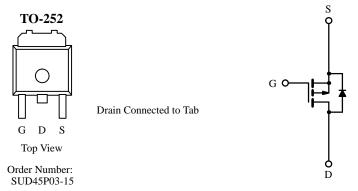


P-Channel 30-V (D-S), 150°C MOSFET

Product Summary

V _{DS} (V)	$\mathbf{r_{DS(on)}}(\Omega)$	$I_{D}(A)^{a}$	
-30	$0.015 @ V_{GS} = -10 V$	±13	
-30	0.024 @ V _{GS} = -4.5 V	±8	





P-Channel MOSFET

Absolute Maximum Ratings ($T_A = 25^{\circ}C$ Unless Otherwise Noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	-30	17	
Gate-Source Voltage		$V_{ m GS}$	±20	V	
Continuous Drain Current ^b	$T_A = 25^{\circ}C$	$\begin{array}{c c} T_A = 25^{\circ}C \\ \hline T_A = 100^{\circ}C \end{array} \qquad I_D$	±13	Δ.	
Continuous Diam Current	$T_A = 100^{\circ}C$		±8		
Pulsed Drain Current		I_{DM}	± 100	A	
Continuous Source Current (Diode Conduction)		I_S	-13		
Maximum Power Dissipation ^b	$T_C = 25^{\circ}C$	P _D	70	W	
Waxiiiuiii I owei Dissipatioii	$T_A=25^{\circ}C$	тр	4 ^a		
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C	

Thermal Resistance Ratings

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	R_{thJA}		30	0.C/W/
Maximum Junction-to-Case	R _{thJC}		1.8	°C/W

Notes

Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70267.

a. Calculated Rating for $T_A = 25^{\circ}$ C, for comparison purposes only. This cannot be used as continuous rating (see Absolute Maximum Ratings and Typical Characteristics).

b. Surface Mounted on FR4 Board, $t \le 10$ sec.

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Specifications ($T_J = 25^{\circ}C$ Unless Otherwise Noted)

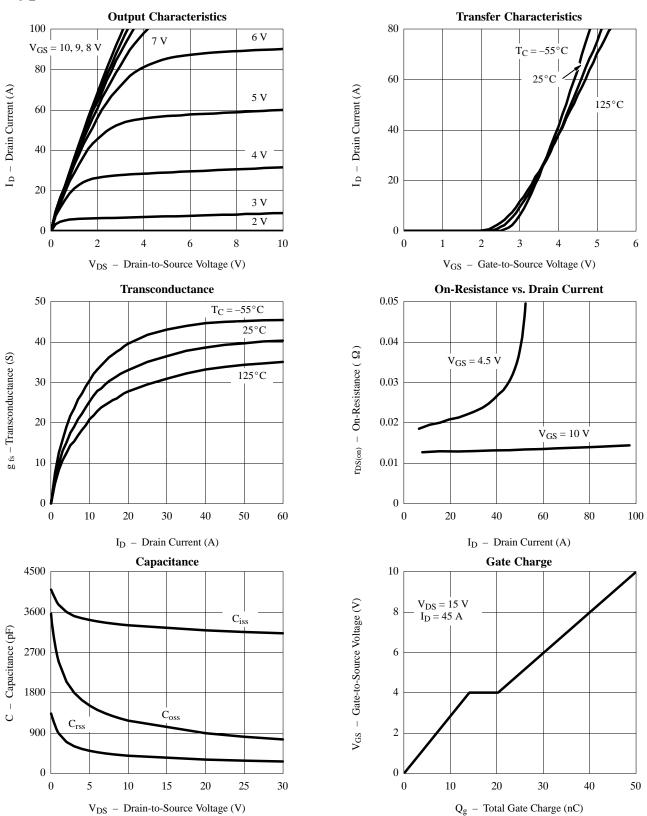
Parameter	Symbol	Test Condition	Min	Typa	Max	Unit	
Static							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = -250 \ \mu\text{A}$	-30			***	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-1.0			V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
7 C. Wi D. C.	,	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$			-1		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125^{\circ}\text{C}$			-50	μΑ	
O St. D. C. dh	,	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-50				
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-20			A	
		$V_{GS} = -10 \text{ V}, I_D = -13 \text{ A}$		0.012	0.015		
Drain-Source On-State Resistance ^b	r _{DS(on)}	$V_{GS} = -10 \text{ V}, I_D = -13 \text{ A}, T_J = 125 ^{\circ}\text{C}$		0.018	0.026	Ω	
		$V_{GS} = -4.5 \text{ V}, I_D = -13 \text{ A}$		0.020	0.024		
Forward Transconductance ^b	g_{fs}	$V_{DS} = -15 \text{ V}, I_D = -13 \text{ A}$	20			S	
Dynamic ^a							
Input Capacitance	C _{iss}			3200		pF	
Output Capacitance	Coss	$V_{GS} = 0 \text{ V}, V_{DS} = -25 \text{ V}, F = 1 \text{ MHz}$		800			
Reverse Transfer Capacitance	C_{rss}			280			
Total Gate Charge ^c	Qg			50	125	nC	
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = -15 \text{ V}, \ V_{GS} = -10 \text{ V}, I_D = -45 \text{ A}$		14			
Gate-Drain Charge ^c	Q_{gd}			6.2			
Turn-On Delay Time ^c	t _{d(on)}			13	20	ns	
Rise Time ^c	t _r	$V_{DD} = -15 \text{ V}, R_L = 0.33 \Omega$		10	20		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong -45 \text{ A}, V_{GEN} = -10 \text{ V}, R_G = 2.4 \Omega$		50	100		
Fall Time ^c	t _f			20	40		
Source-Drain Diode Ratings and	Characterist	ic $(T_C = 25^{\circ}C)$	•				
Pulsed Current	I_{SM}				100	A	
Diode Forward Voltage ^b	V_{SD}	$I_F = -45 \text{ A}, V_{GS} = 0 \text{ V}$		1.0	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = -45 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		55	100	ns	

Notes

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width $\leq 300 \,\mu\text{s}$, duty cycle $\leq 2\%$.
- c. Independent of operating temperature.



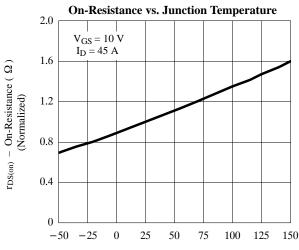
Typical Characteristics (25°C Unless Otherwise Noted)

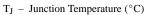


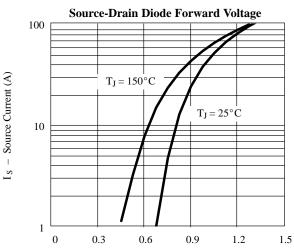
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Typical Characteristics (25°C Unless Otherwise Noted)

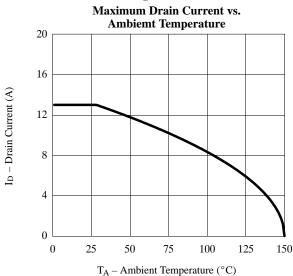




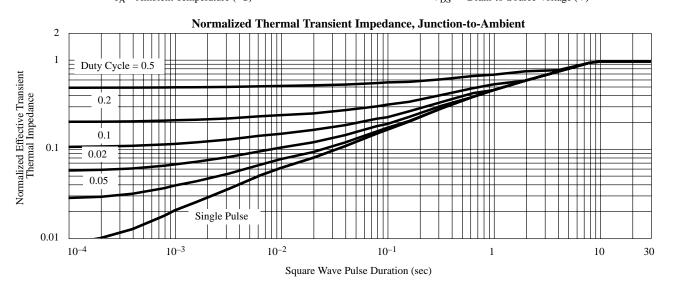


V_{SD} - Source-to-Drain Voltage (V)

Thermal Ratings



Safe Operating Area 500 100 Limited - Drain Current (A) by r_{DS(on)} 10, 100 μs 10 1 ms ----10 ms 100 ms $T_A=25\,^{\circ}C$ -----Single Pulse 1 s dc 0.1 0.1 100 V_{DS} – Drain-to-Source Voltage (V)





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